

ABSTRACT OF THE DISCLOSURE

There is provided an electroless Ni-B plating liquid for forming, a Ni-B alloy film on at least part of the interconnects
5 of an electronic device having an embedded interconnect structure, the electroless Ni-B plating liquid comprising nickel ions, a complexing agent for nickel ions, a reducing agent for nickel ions, and ammoniums (NH_4^+). The electroless Ni-B plating liquid can lower the boron content of the resulting plated film without increasing
10 the plating rate and form a Ni-B alloy film having an FCC crystalline structure.